

1. General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT223 surface mountable plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate
- Surface mountable package

3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

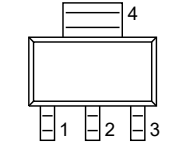

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--------------------------------------|---|-----|-----|-----|------------------------|
| V_{RRM} | repetitive peak reverse voltage | | - | - | 400 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{sp} \leq 114\text{ °C}$; Fig. 1 | - | - | 0.5 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_{sp} \leq 114\text{ °C}$; Fig. 2 ; Fig. 3 | - | - | 0.8 | A |
| I_{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 8 | A |
| | | half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$ | - | - | 9 | A |
| T_j | junction temperature | | - | - | 125 | °C |
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 9 | - | 3 | 12 | μA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 268\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | - | 150 | - | $\text{V}/\mu\text{s}$ |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|---|
| 1 | K | cathode |  <p>SC-73 (SOT223)</p> |  <p>A — K G sym037</p> |
| 2 | A | anode | | |
| 3 | G | gate | | |
| 4 | mb | mounting base; connected to anode | | |

6. Ordering information

Table 3. Ordering information

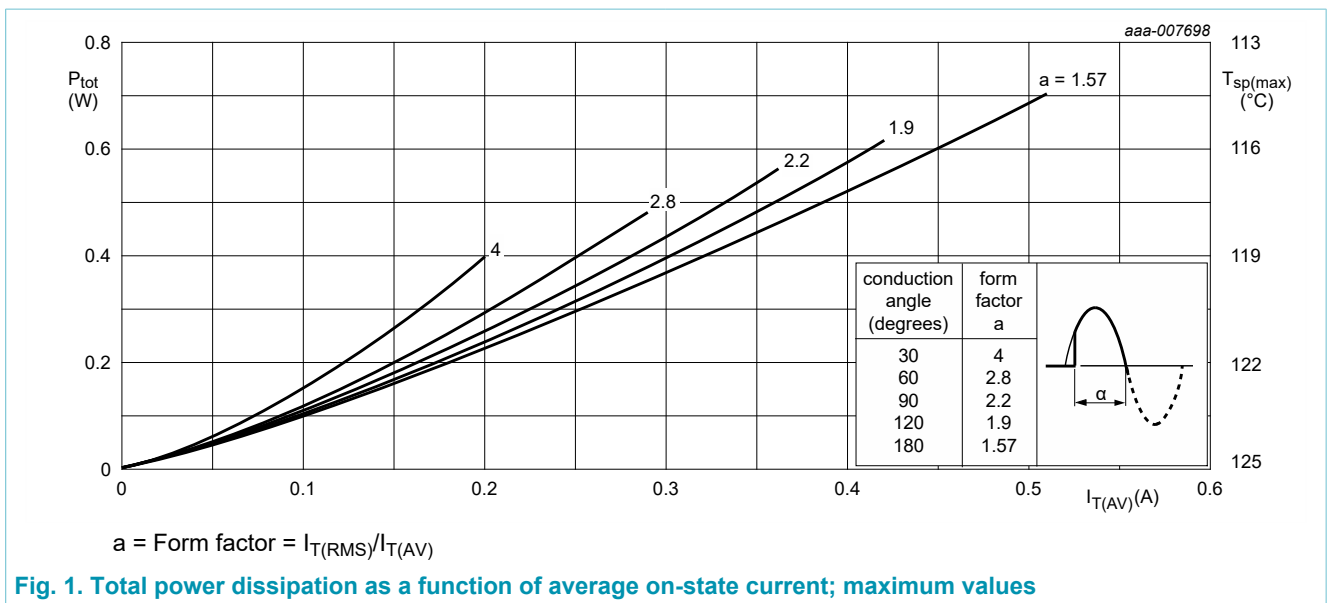
| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| EC103D1W | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|---|-----|------|--------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 400 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | 400 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{sp} \leq 114\text{ }^{\circ}\text{C}$; Fig. 1 | - | 0.5 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_{sp} \leq 114\text{ }^{\circ}\text{C}$; Fig. 2; Fig. 3 | - | 0.8 | A |
| I_{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4; Fig. 5 | - | 8 | A |
| | | half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$ | - | 9 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; sine-wave pulse | - | 0.32 | A ² s |
| dl_T/dt | rate of rise of on-state current | $I_T = 2\text{ A}$; $I_G = 0.01\text{ A}$; $dl_G/dt = 0.1\text{ A}/\mu\text{s}$ | - | 50 | A/ μs |
| I_{GM} | peak gate current | | - | 1 | A |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_{GM} | peak gate power | | - | 2 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.1 | W |
| T_{stg} | storage temperature | | -40 | 150 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | - | 125 | $^{\circ}\text{C}$ |



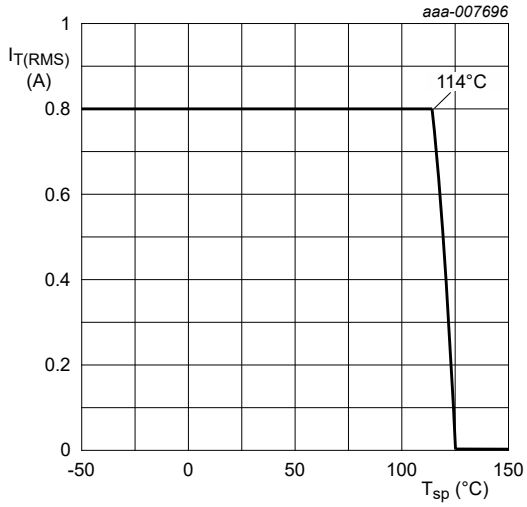


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

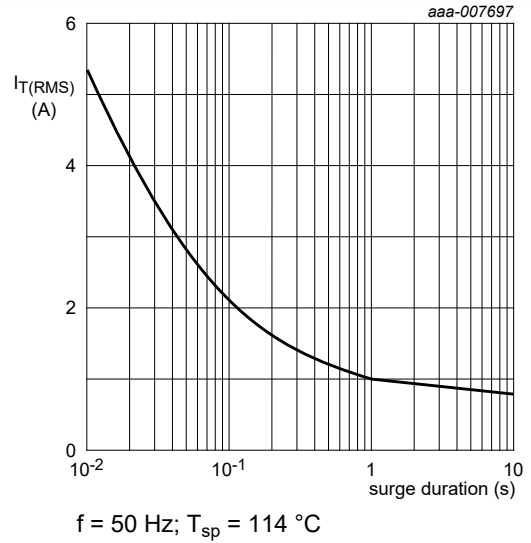


Fig. 3. RMS on-state current as a function of surge duration; maximum values

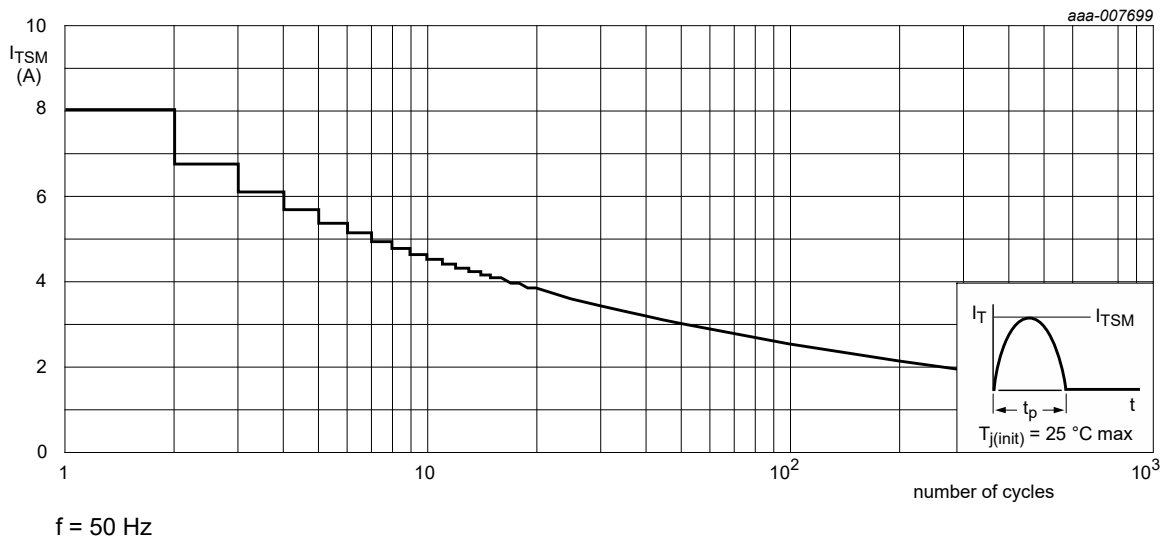
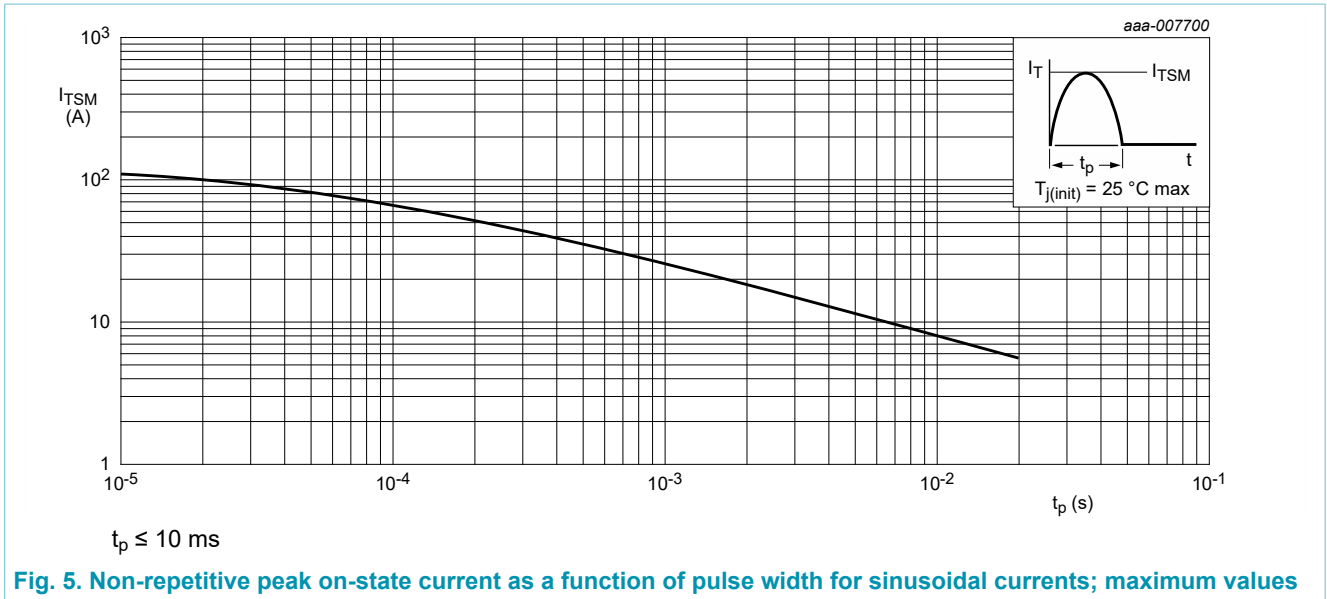


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|---|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | Fig. 6 | - | - | 15 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | printed circuit board mounted; minimum pad area; in free air; Fig. 7 | - | 70 | - | K/W |
| | | printed circuit board mounted; minimum footprint; in free air; Fig. 8 | - | 156 | - | K/W |

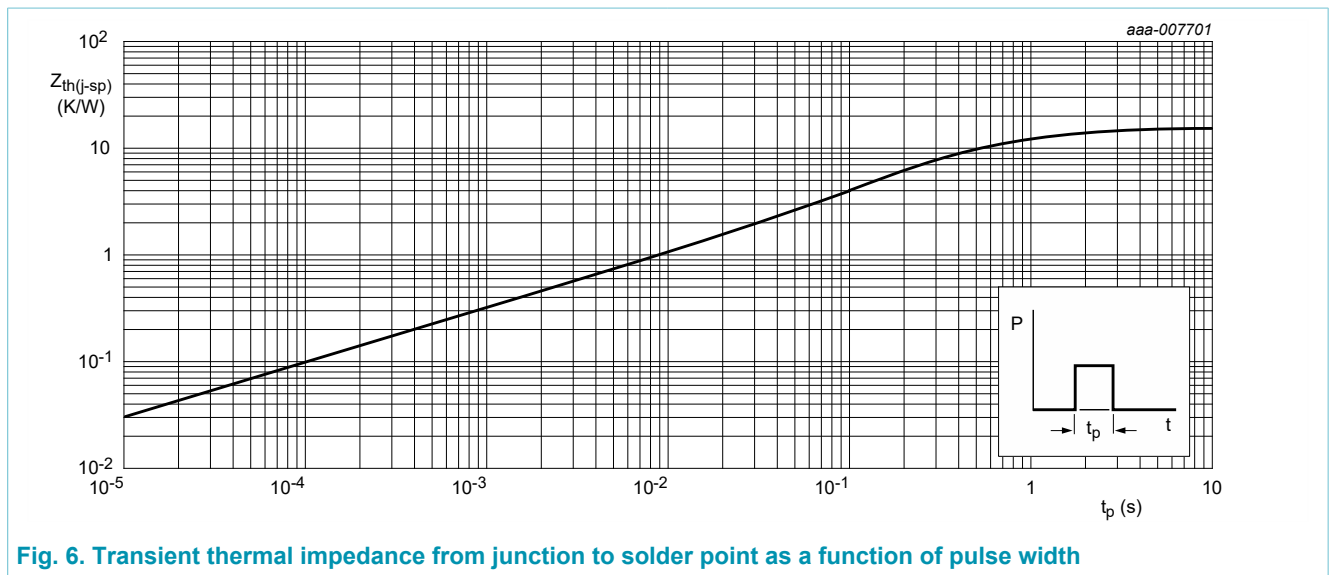
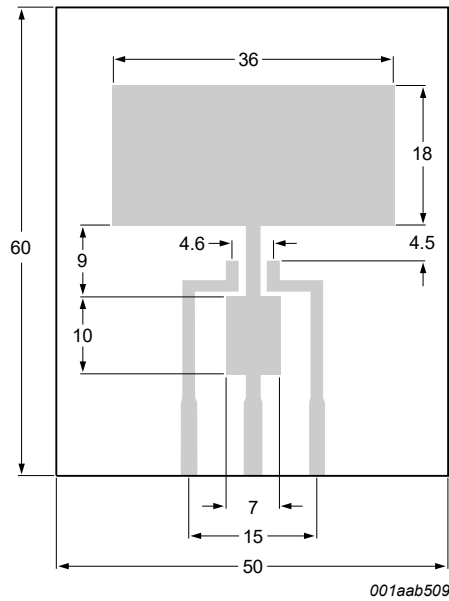
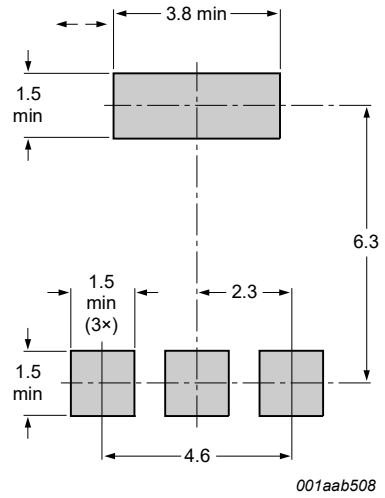


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm
 Printed circuit board:
 FR4 epoxy glass (1.6 mm thick), copper laminate
 (35 um thick)

Fig. 7. Printed circuit board pad area: SOT223



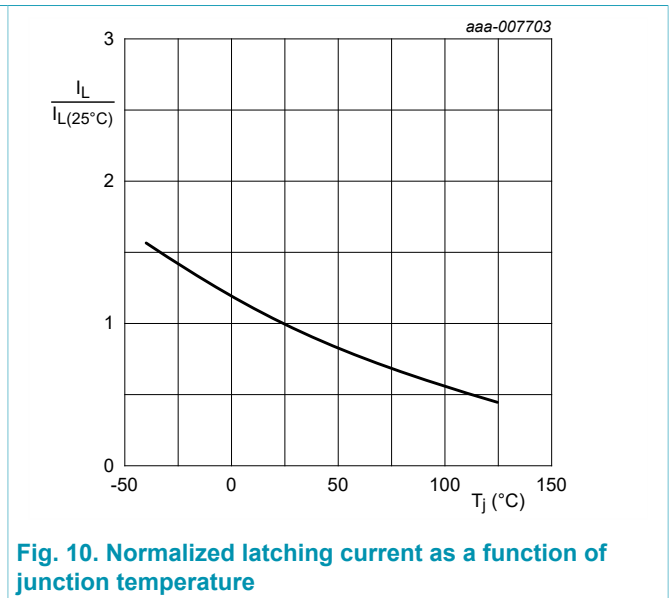
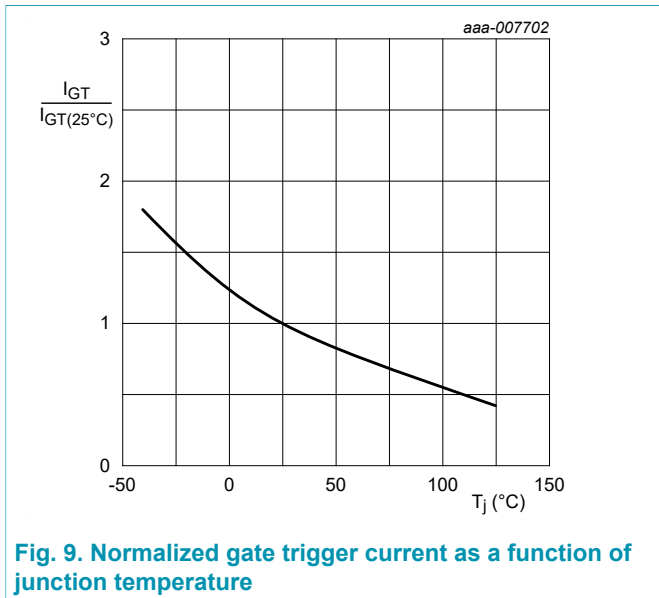
All dimensions are in mm

Fig. 8. Minimum footprint SOT223

9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|---|-----|------|------|------------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9 | - | 3 | 12 | μA |
| I_L | latching current | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10 | - | 2 | 6 | mA |
| I_H | holding current | $V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11 | - | 2 | 5 | mA |
| V_T | on-state voltage | $I_T = 1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 12 | - | 1.2 | 1.35 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 13 | - | 0.5 | 0.8 | V |
| | | $V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C};$ Fig. 13 | 0.2 | 0.3 | - | V |
| I_D | off-state current | $V_D = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}$ | - | 0.05 | 0.1 | mA |
| I_R | reverse current | $V_R = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}$ | - | 0.05 | 0.1 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 268\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit | - | 150 | - | V/ μs |



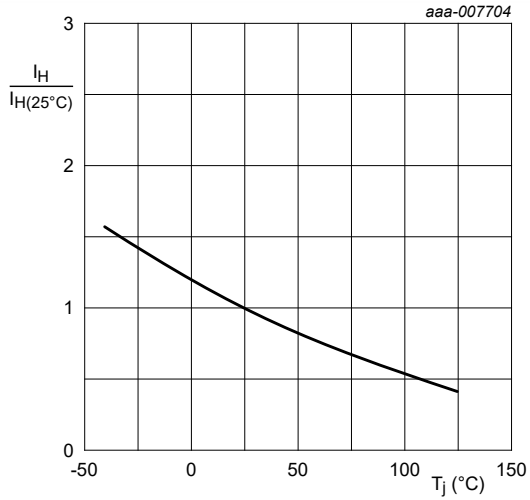
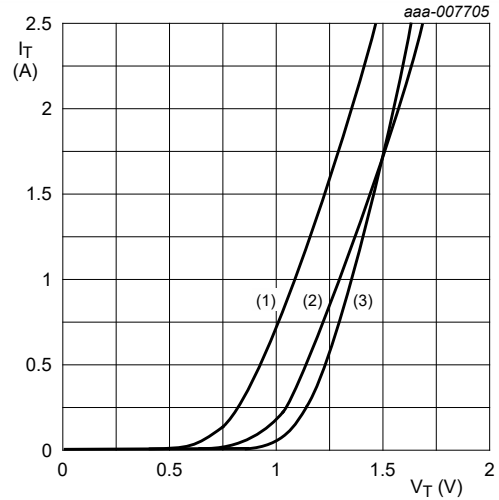


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 0.987 \text{ V}; R_s = 0.3125 \Omega$
 (1) $T_j = 125^\circ\text{C}$; typical values
 (2) $T_j = 125^\circ\text{C}$; maximum values
 (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 12. On-state current as a function of on-state voltage

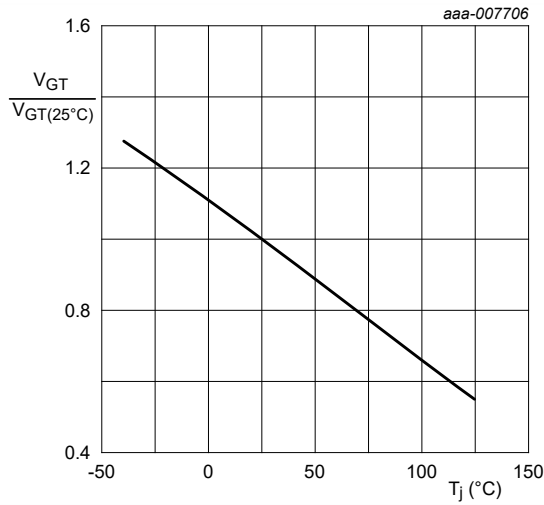


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

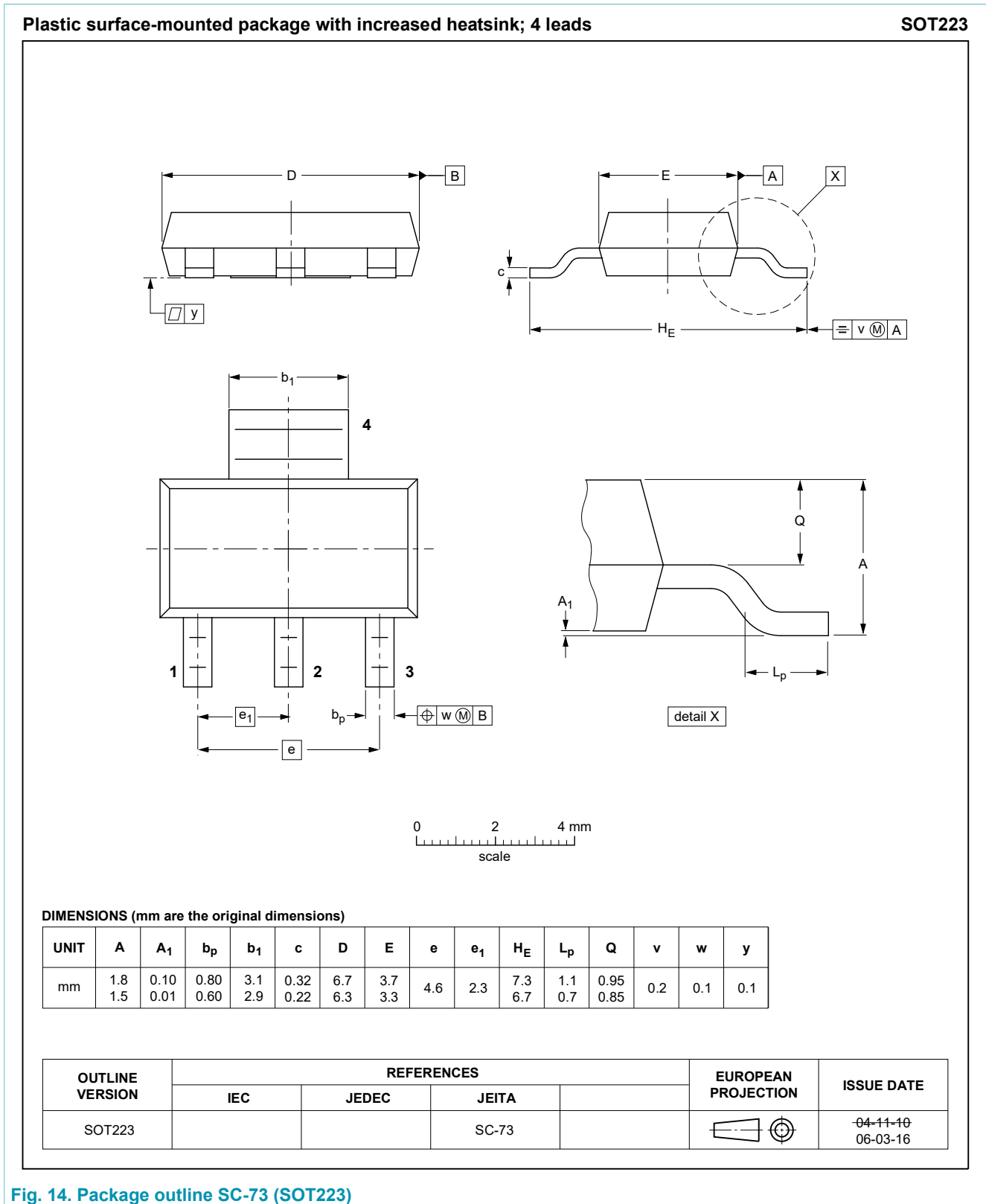


Fig. 14. Package outline SC-73 (SOT223)

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|--------------------------------|--------------------|---|
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- [2] The term 'short data sheet' is explained in section "Definitions".
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